

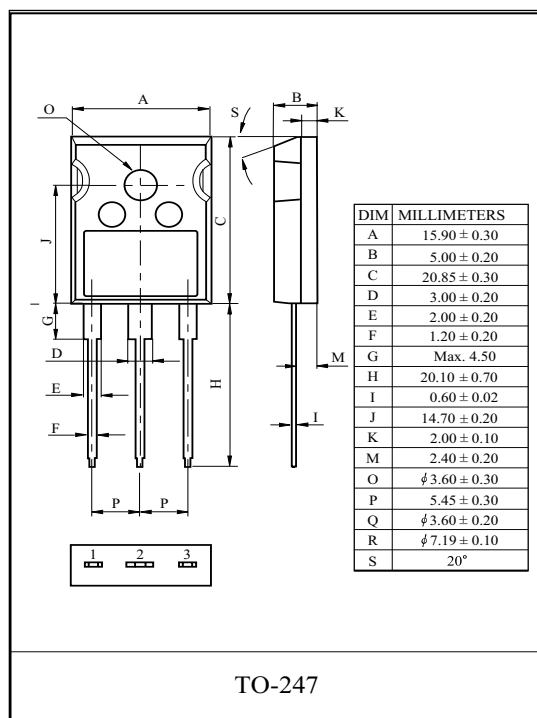
General Description

KEC NPT Trench IGBTs offer low switching losses, high energy efficiency and short circuit ruggedness.

It is designed for applications such as motor control, uninterrupted power supplies(UPS), general inverters.

FEATURES

- High speed switching
- High system efficiency
- Short Circuit Withstand Times 10us
- Extremely enhanced avalanche capability



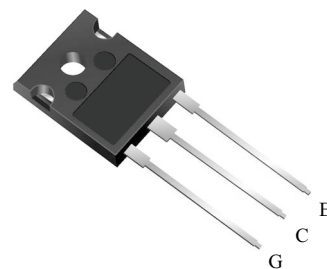
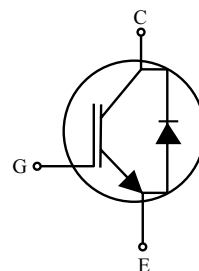
MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V_{CES}	600	V
Gate-Emitter Voltage		V_{GES}	± 20	V
Collector Current	@Tc=25	I_C	100	A
	@Tc=100		50	A
Pulsed Collector Current		I_{CM}^*	150	A
Diode Continuous Forward Current	@Tc=100	I_F	50	A
Diode Maximum Forward Current		I_{FM}	100	A
Maximum Power Dissipation	@Tc=25	P_D	345	W
	@Tc=100		138	W
Maximum Junction Temperature		T_j	150	
Storage Temperature Range		T_{stg}	-55 to + 150	

*Repetitive rating : Pulse width limited by max. junction temperature

THERMAL CHARACTERISTIC

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case (IGBT)	R_{thJC}	0.36	/W
Thermal Resistance, Junction to Case (DIODE)	R_{thJC}	1.0	/W
Thermal Resistance, Junction to Ambient	R_{thJA}	40	/W



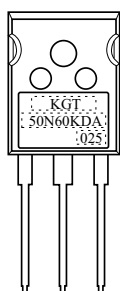
KGT50N60KDA

ELECTRICAL CHARACTERISTICS (Ta=25)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Static							
Collector-Emitter Breakdown Voltage	BV _{CES}	V _{GE} =0V , I _C =250 μA	600	-	-	V	
Collector Cut-off Current	I _{CES}	V _{GE} =0V, V _{CE} =600V	-	-	250	μA	
Gate Leakage Current	I _{GES}	V _{CE} =0V, V _{GE} = ± 20V	-	-	± 100	nA	
Gate Threshold Voltage	V _{GE(th)}	V _{GE} =V _{CE} , I _C =5mA	5.0	6.0	7.0	V	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} =15V, I _C =50A	-	1.90	2.2	V	
		V _{GE} =15V, I _C =100A	-	2.6	-	V	
		V _{GE} =15V, I _C =50A, T _C = 125	-	2.20	-	V	
Dynamic							
Total Gate Charge	Q _g	V _{CC} =300V, V _{GE} =15V, I _C = 50A	-	200	-	nC	
Gate-Emitter Charge	Q _{ge}		-	30	-	nC	
Gate-Collector Charge	Q _{gc}		-	100	-	nC	
Turn-On Delay Time	t _{d(on)}	V _{CC} =300V, I _C =50A, V _{GE} =15V,R _G =10 Ω Inductive Load, T _C = 25 (Note 1)	-	95	-	ns	
Rise Time	t _r		-	85	-	ns	
Turn-Off Delay Time	t _{d(off)}		-	340	-	ns	
Fall Time	t _f		-	40	-	ns	
Turn-On Switching Loss	E _{on}		-	1.40	-	mJ	
Turn-Off Switching Loss	E _{off}		-	0.80	-	mJ	
Total Switching Loss	E _{ts}		-	2.2	-	mJ	
Turn-On Delay Time	t _{d(on)}		V _{CC} =300V, I _C =50A, V _{GE} =15V, R _G =10 Ω Inductive Load, T _C = 125 (Note 1)	-	95	-	ns
Rise Time	t _r			-	90	-	ns
Turn-Off Delay Time	t _{d(off)}	-		350	-	ns	
Fall Time	t _f	-		50	-	ns	
Turn-On Switching Loss	E _{on}	-		1.5	-	mJ	
Turn-Off Switching Loss	E _{off}	-		1.2	-	mJ	
Total Switching Loss	E _{ts}	-		2.7	-	mJ	
Input Capacitance	C _{ies}	V _{CE} =30V, V _{GE} =0V, f=1MHz	-	4000	-	pF	
Ouput Capacitance	C _{oes}		-	250	-	pF	
Reverse Transfer Capacitance	C _{res}		-	130	-	pF	
Short Circuit Withstand Time	t _{sc}	V _{CC} =300V, V _{GE} =15V, T _C =100	10	-	-	μs	

Note 1 : Energy loss include tail current and diode reverse recovery.

Marking



- ① Device Mark 1
- ② Device Mark 2
- ③ Lot No

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ELECTRICAL CHARACTERISTIC OF DIODE

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Diode Forward Voltage	V _F	I _F = 50A	T _C =25	-	1.7	2.5	V
			T _C =100	-	2.0	-	
Diode Reverse Recovery Time	t _{rr}	I _F = 50A di/dt = 600A/ μs	T _C =25	-	100	200	ns
			T _C =100	-	120	-	
Diode Peak Reverse Recovery Current	I _{rr}		T _C =25	-	20	40	A
			T _C =100	-	30	-	
Diode Reverse Recovery Charge	Q _{rr}		T _C =25	-	1.2	3.5	μC
			T _C =100	-	2.2	-	

Fig 1. Saturation Voltage Characteristics

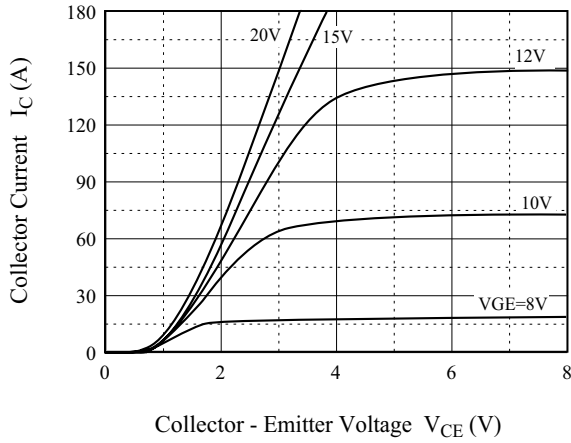


Fig 2. Saturation Voltage Characteristics

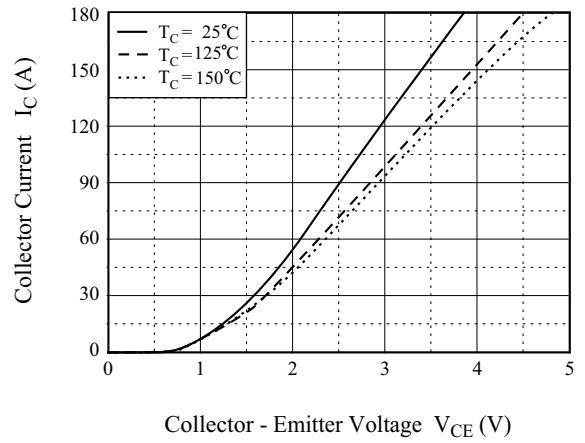


Fig 3. Saturation Voltage vs. Case Temperature

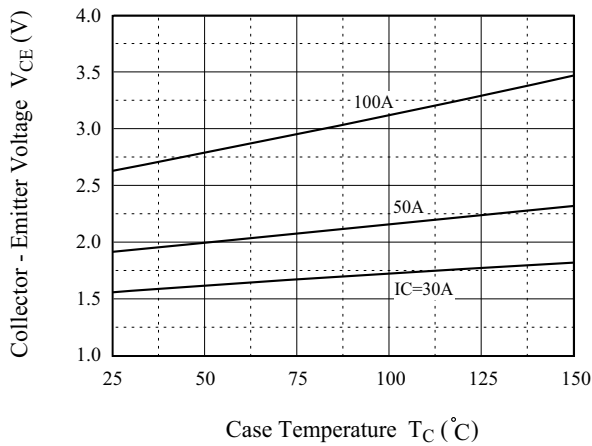


Fig 4. Saturation Voltage vs. V_{GE}

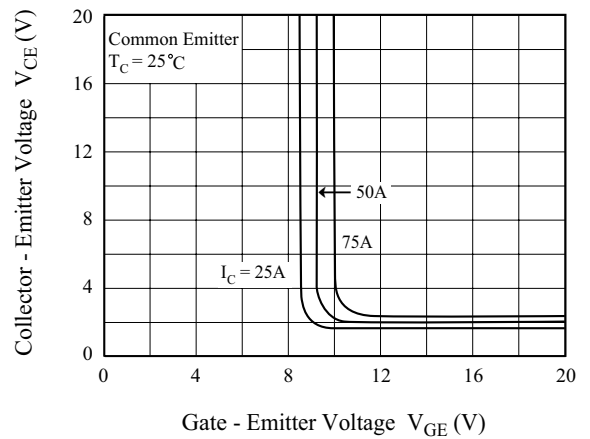


Fig 5. Saturation Voltage vs. V_{GE}

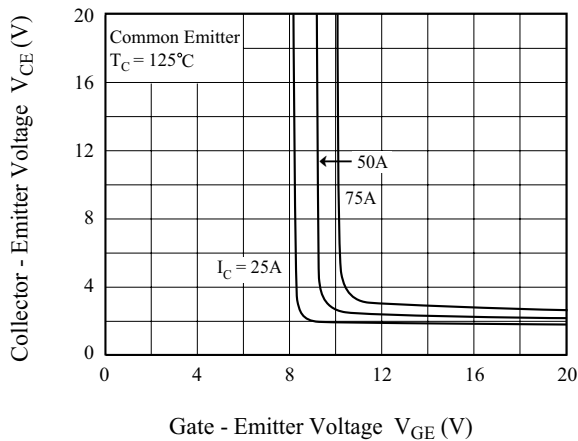


Fig 6. Capacitance Characteristics

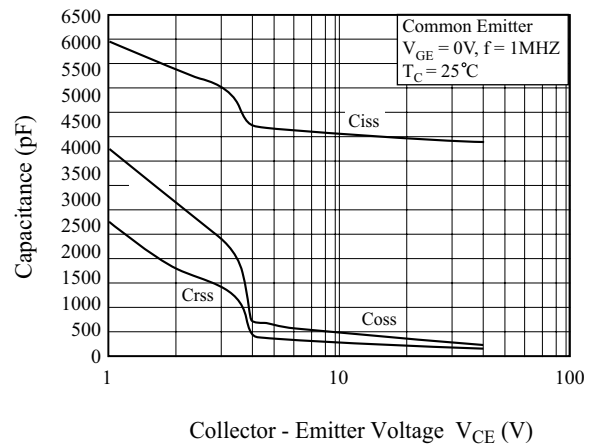


Fig 7. Turn-On Characteristics vs. Gate Resistance

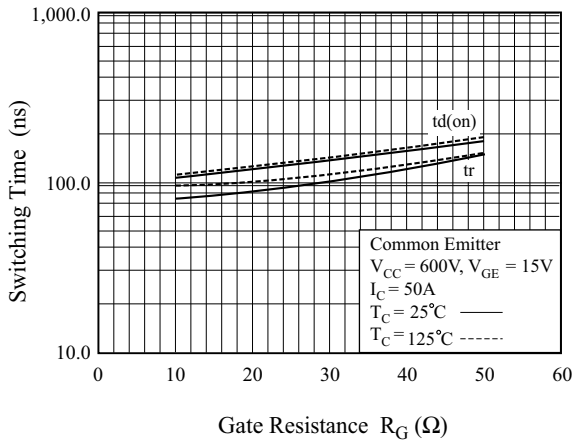


Fig 8. Turn-Off Characteristics vs. Gate Resistance

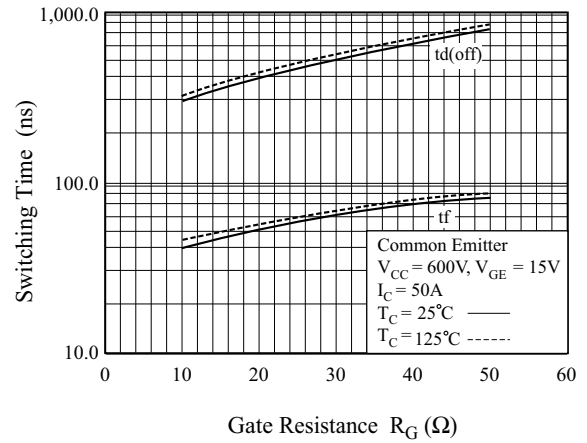


Fig 9. Switching Loss vs. Gate Resistance

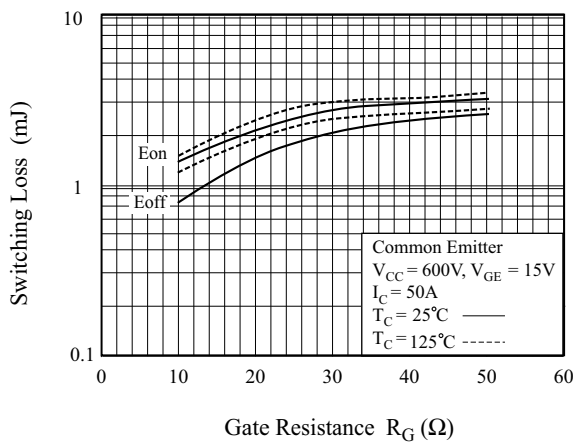


Fig 10. Turn-On Characteristics vs. Collector Current

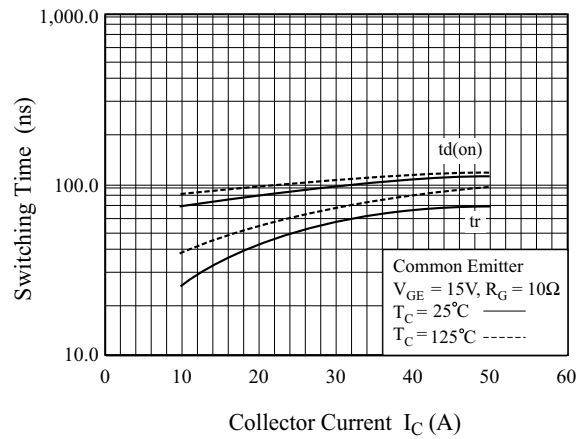


Fig 11. Turn-Off Characteristics vs. Collector Current

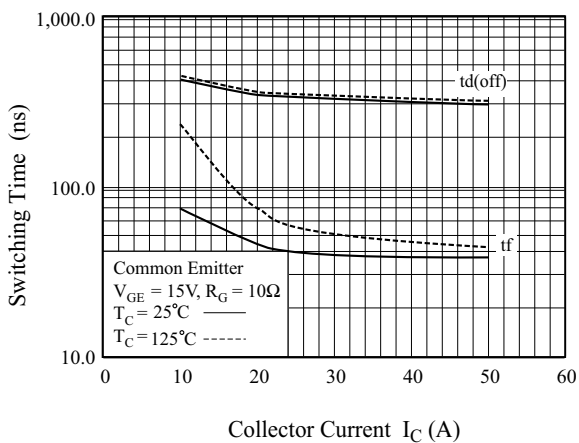


Fig 12. Switching Loss vs. Collector Current

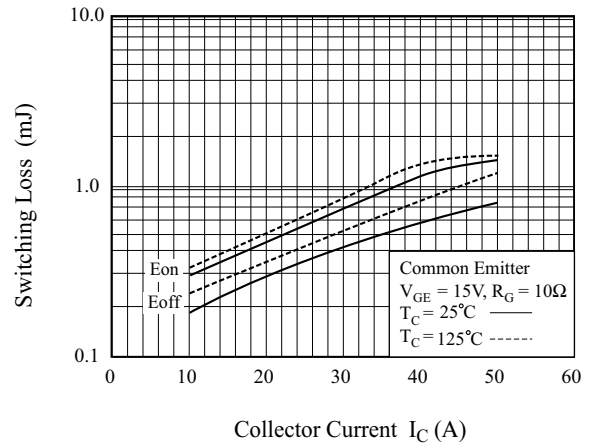


Fig 13. Gate Charge Characteristics

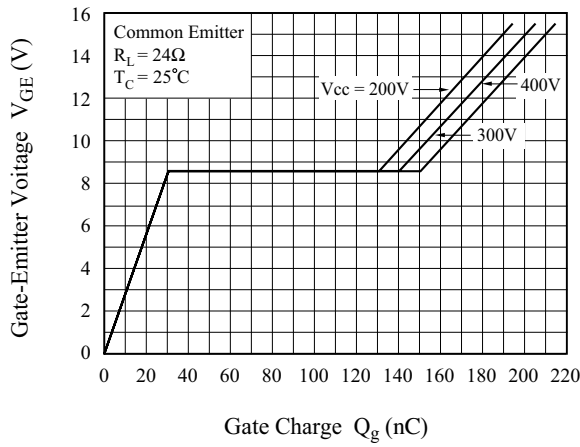


Fig 14. SOA Characteristics

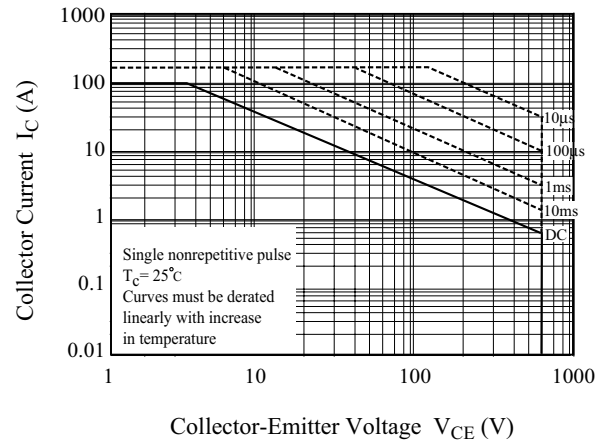


Fig 15. Turn-Off SOA

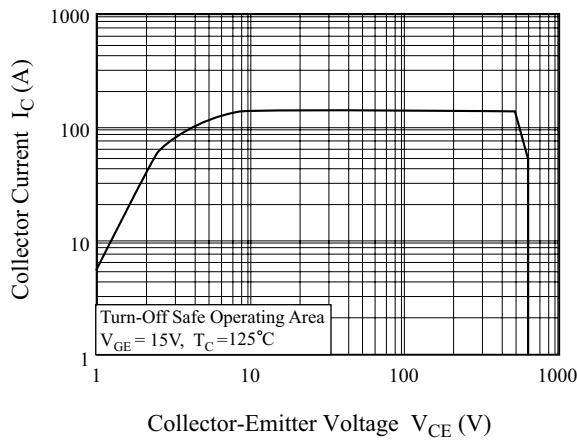
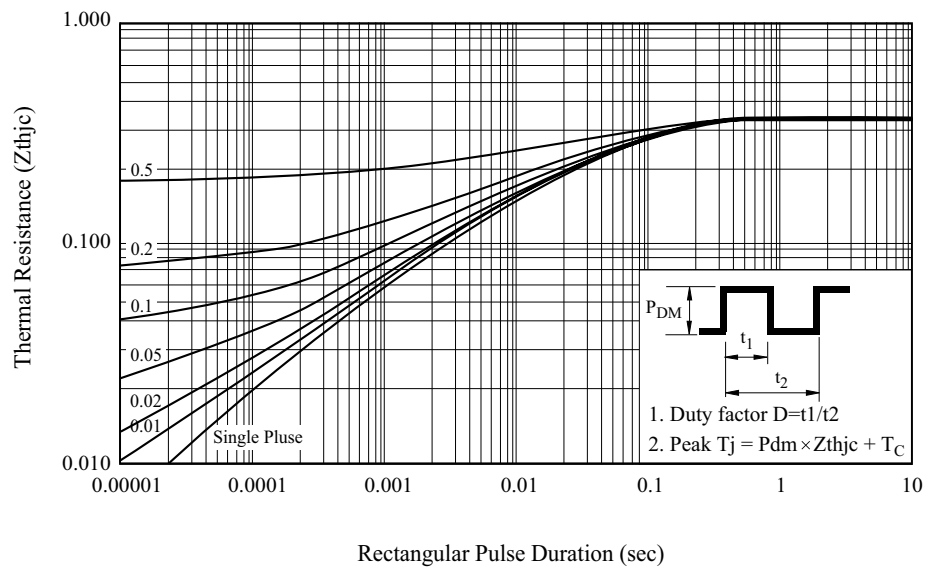


Fig 16. Transient Thermal Impedance of IGBT



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Fig 17. Forward Characteristics

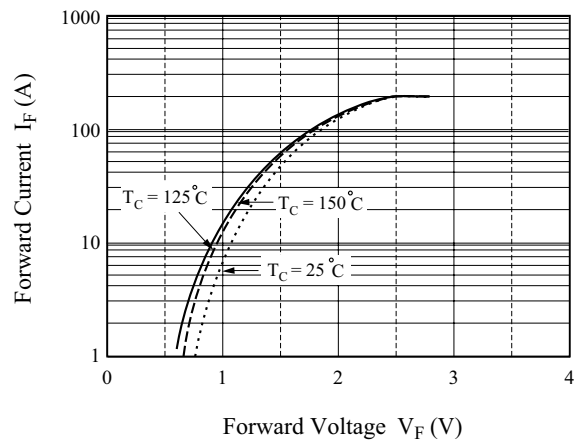


Fig 18. Reverse Recovery Current

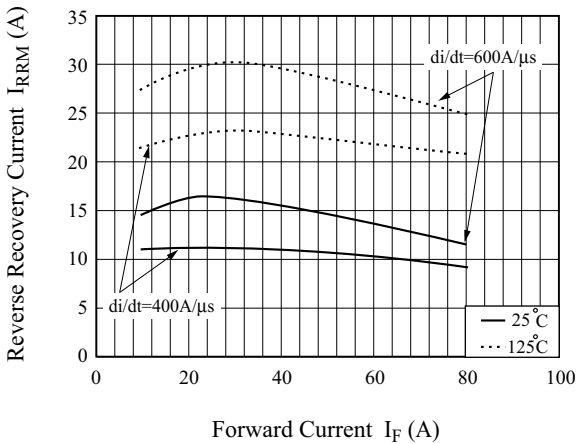


Fig 19. Reverse Recovery Time

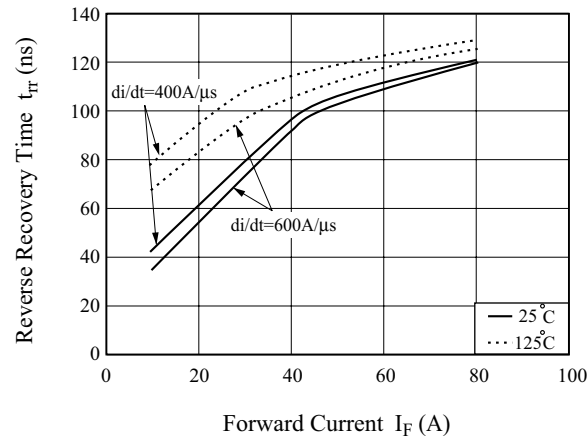


Fig 20. Switching Test Circuit

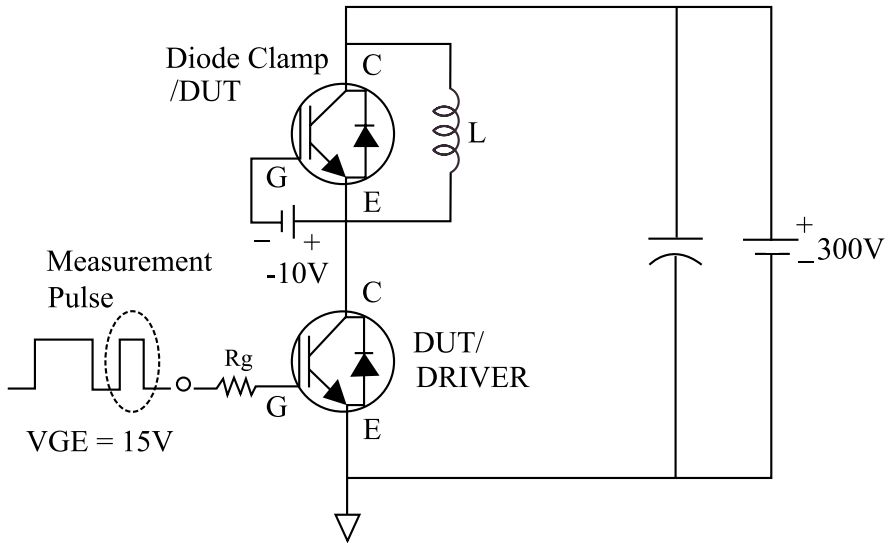


Fig 21. Definition Switching Time & Loss

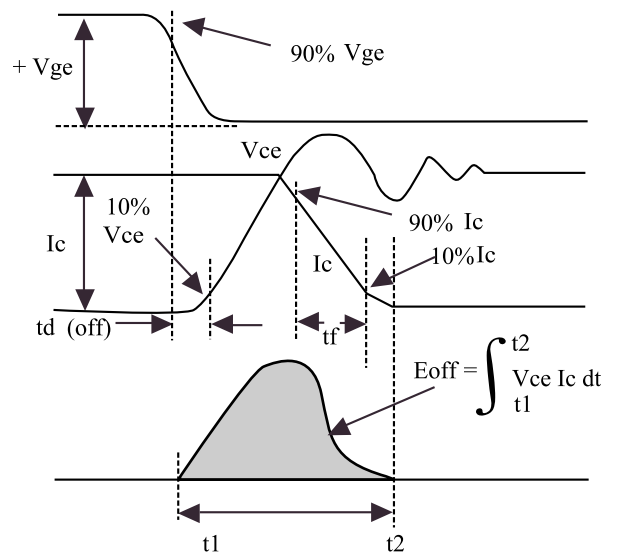
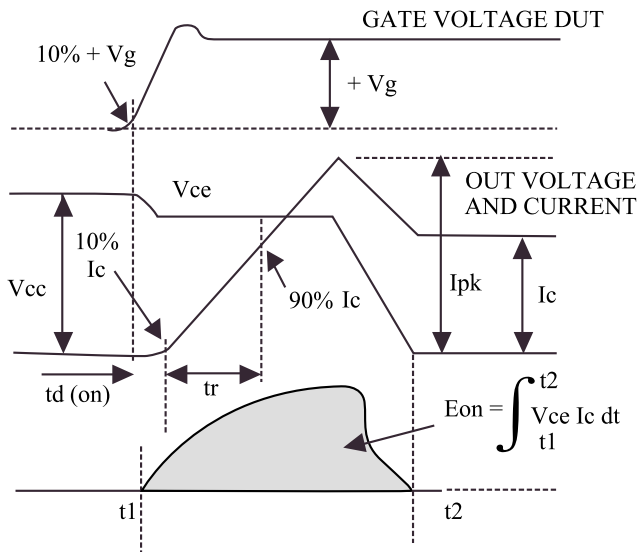


Fig 22. Definition Diode Switching Time

